**Features:**

Two anti-parallel thyristors on one
Si-wafer
Hermetic metal cases with ceramic
insulators
Capsule packages for double sided
cooling

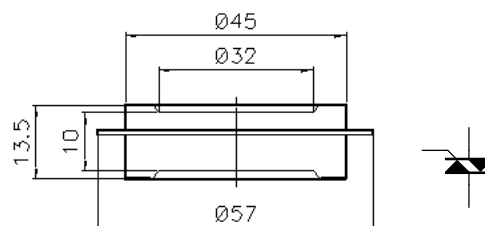
Typical Applications

High power industrial and power
transmission
DC and AC motor control
AC controllers

Part No. Y35KSEA-KA32

$I_{T(RMS)}$	730A	
V_{DRM}, V_{RRM}	500V	800V
	1000V	1200V
	1400V	1600V
	1800V	

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(RMS)}$	RMS current	50Hz sine wave Double side cooled, $T_C=55^\circ\text{C}$ $T_C=85^\circ\text{C}$	125			1060 730	A
V_{DRM}	Repetitive peak reverse voltage	$V_{DRM} t_p=10\text{ms}$ $V_{DSM}=V_{DRM}+100\text{V}$	125	500		1800	V
I_{DRM}	Repetitive peak current	at V_{DRM}	125			40	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			7	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$				245	$\text{A}^2\text{s}\cdot 10^3$
V_{TO}	Threshold voltage		125			0.90	V
r_T	On-state slope resistance					1.02	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=750\text{A}$, $F=15\text{kN}$	125			2.70	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			50	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 1000A, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$ Repetitive	125			50	A/μs
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$	25	20		300	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			20		300	mA
I_L	Latching current					500	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	double side cooled Clamping force 15kN				0.035	C/W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.010	
F_m	Mounting force			10		20	kN
T_{vj}	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				110		g
Outline	KA32						

Outline:

TECHSEM reserves the right to change specifications without notice.